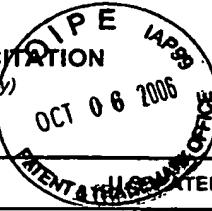


INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>				Docket Number (Optional) F05-420-US	Application Number 10/564,416		
				Applicant(s) Masanobu ANDO, et al.			
 Filing Date January 12, 2006				Group Art Unit 2811			
U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
U.S. PATENT APPLICATION PUBLICATIONS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
FOREIGN PATENT DOCUMENTS							
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation
							YES
		EP 0 662 739	07/12/1995	Europe previously submitted with IDS dated 4/12/06			
		11-026812	01/29/1999	Japan previously submitted with IDS dated 4/12/06			
OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>							
		European Search Report dated June 2, 2006					
		Kneissl, Michael, et al., "Continuous-wave ultraviolet InGaN/InAlGaN multiple-quantum-well laser diodes", Applied Physics Letters, AIP, American Institute of Physics, Melville, NY, US, Vol. 82, No. 15, April 14, 2003, Pages 2386-2388, 012033738 previously submitted with IDS dated 4/12/06					
EXAMINER /Sara Crane/		DATE CONSIDERED 12/23/2006					
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

INFORMATION DISCLOSURE CITATION <small>(Use several sheets if necessary)</small>			ATTY DOCKET NO. F05-420-US APPLICANT(S) Masanobu ANDO, et al. FILING DATE January 12, 2006		APPLICATION NO. 10/564,416 GROUP ART UNIT 2811			
 U.S. PATENT & TRADEMARK OFFICE INVENTION & TRADEMARK DOCUMENTS								
U.S. PATENT APPLICATION PUBLICATIONS								
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
FOREIGN PATENT DOCUMENTS								
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)								
		<small>Nakamura, et al., "InGaN/GaN/AlGaN-based laser diodes with modulation-doped strained-layer superlattices grown on an epitaxially-laterally overgrown GaN substrate", Applied Physics Letter, AIP, American Institute of Physics, Melville, NY, U.S., Vol. 72, No. 2, January 12, 1998</small>						
		<small>Previously submitted with I 65 dated 4/12/06</small>						
EXAMINER /Sara Crane/			DATE CONSIDERED		12/23/2006			
<small>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small>								